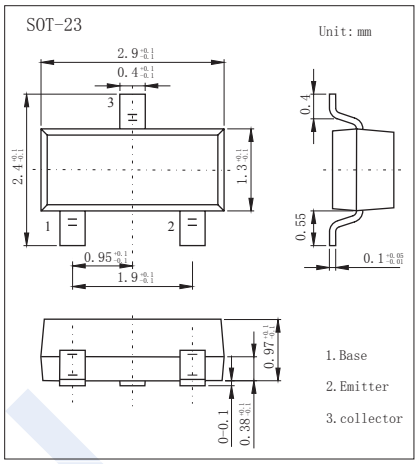
PNP Transistors

2SA1121



■ Features

- Low frequency amplifier
- Complementary pair with 2SC2618

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-35	V
Collector to emitter voltage	V_{CEO}	-35	V
Emitter to base voltage	V_{EBO}	-4	V
Collector current	I_C	-500	mA
Collector power dissipation	P_C	150	mW
Junction temperature	Tj	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -100 uA， I_E=0	-35			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -1 mA， I_B=0	-35			
Emitter - base breakdown voltage	V_{EBO}	I_E= -100 μ A， I_C=0	-4			
Collector-base cut-off current	I_{CBO}	V_{CB}= -30 V , I_E=0			-0.1	uA
Emitter cut-off current	I_{EBO}	V_{EB}= -4V , I_C=0			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-150 mA, I_B=-15mA		-0.2	-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-150 mA, I_B=-15mA			-1.2	
Base-emitter voltage	V_{BE}	I_C=-10 mA, V_{CE}=-3V		-0.64		
DC current transfer ratio	h_{FE}	I_C=-10 mA, V_{CE}=-3V	100		320	
		I_C=-500 mA, V_{CE}=-3V	10			

■ $h_{FE(1)}$ Classification

Marking	SC	SD
hFE	100～200	160～320

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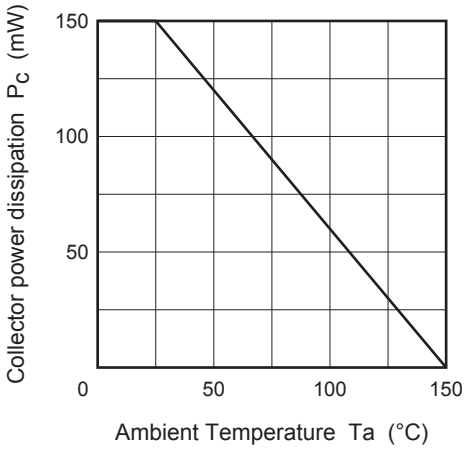
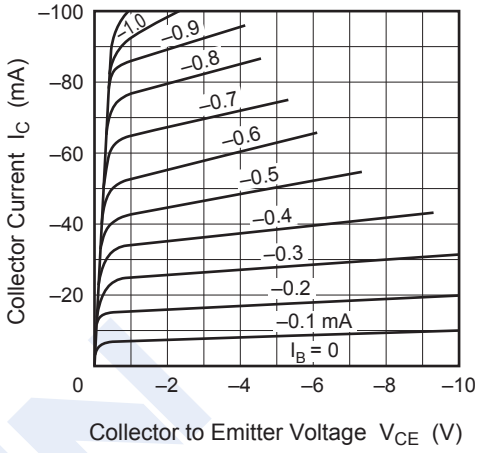
■ Typical Characterisitics

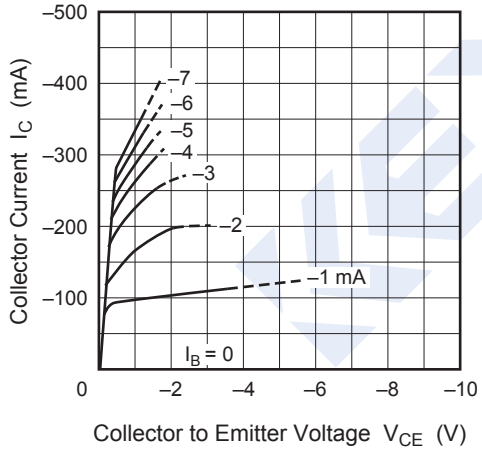
Maximum Collector Dissipation Curve



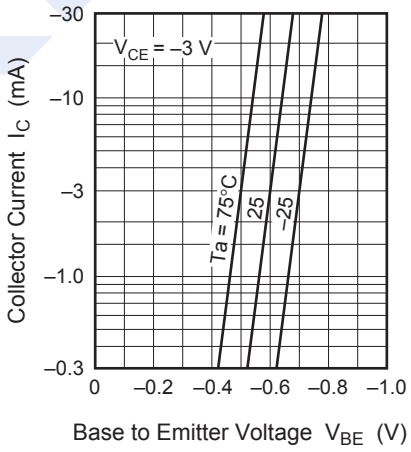
Typical Output Characteristics (1)



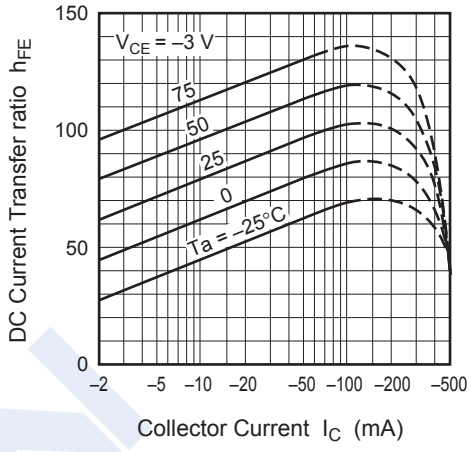
Typical Output Characteristics (2)



Typical Transfer Characteristics



DC Current Transfer Ratio vs. Collector Current



Gain Bandwidth Product vs. Collector Current